

Title (en)

SEMICONDUCTOR COMPONENT WITH CONTACTS PROVIDED ON THE LOWER SIDE THEREOF, AND METHOD FOR PRODUCING THE SAME

Title (de)

HALBLEITERBAUELEMENT MIT AN DER UNTERSEITE BEFINDLICHEN KONTAKTEN UND VERFAHREN ZUR HERSTELLUNG

Title (fr)

COMPOSANT A SEMICONDUCTEURS PRESENTANT DES CONTACTS SITUÉS AU NIVEAU DE SA FACE INFÉRIEURE, ET SON PROCÉDÉ DE PRODUCTION

Publication

EP 1269539 A1 20030102 (DE)

Application

EP 01911410 A 20010131

Priority

- DE 0100386 W 20010131
- DE 10004410 A 20000202

Abstract (en)

[origin: WO0157924A1] The invention relates to a semiconductor component that comprises a housing with a first main surface and a second main surface opposite the first surface, said housing substantially enclosing at least one semiconductor chip. Said semiconductor chip has a first metallization on a first main side. A second main side of the semiconductor chip reaches the second main surface of the semiconductor component. The first metallization of the semiconductor chip is linked via conductors with contacts that are also enclosed by the housing and that reach the second main side. The semiconductor chip is further provided on the second main side with a second metallization that transmits signals.

IPC 1-7

H01L 23/31

IPC 8 full level

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C-Set (source: EP US)

1. **H01L 2224/48475 + H01L 2924/01079**
2. **H01L 2924/00014 + H01L 2224/45015 + H01L 2924/207**
3. **H01L 2924/181 + H01L 2924/00**
4. **H01L 2224/48091 + H01L 2924/00014**
5. **H01L 2224/49171 + H01L 2224/48465 + H01L 2924/00**
6. **H01L 2224/48465 + H01L 2224/48091 + H01L 2924/00**
7. **H01L 2224/48465 + H01L 2224/48247 + H01L 2924/00**
8. **H01L 2924/12042 + H01L 2924/00**
9. **H01L 2224/05599 + H01L 2924/00014**
10. **H01L 2224/854 + H01L 2924/00014**
11. **H01L 2924/00014 + H01L 2224/45099**

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See references of WO 0157924A1

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DOCDB simple family (publication)

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